

H. Display and Imaging Technologies 분과

2020년 2월 14일(금), 10:45-12:30 / Room C (사파이어 I, 5층)

■ [FC2-H] Oxide Thin-Film Transistors

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FC2-H-1 10:45-11:15	<p>[초청]</p> <p>Optoelectronics based on the Quantum-dots and Oxide Semiconductors</p> <p>Seong Jun Kang <i>Department of Advanced Materials Engineering for Information and Electronics, Kyung Hee University</i></p>
FC2-H-2 11:15-11:30	<p>Impact of Oxidants on Formation of HfO₂ Gate Insulator Prepared by Atomic-layer Deposition for In-Ga-Zn-O Thin Film Transistor</p> <p>Se-na Choi and Sung-min Yoon <i>Department of Advanced Materials Engineering for Information and Electronics, Kyung Hee University</i></p>
FC2-H-3 11:30-11:45	<p>Thin Film Transistor Characteristics of In-Sn-Ga-O Semiconductor at Low Temperature.</p> <p>Changyong Oh and Bo Sung Kim <i>Department of Applied Physics, Korea University</i></p>
FC2-H-4 11:45-12:00	<p>Effects of Lateral Carrier Diffusion and Source-Drain Parasitic Resistance in Self-Aligned Top-Gate Coplanar InGaZnO Thin-Film Transistors</p> <p>Dae-hwan Kim¹, Sae-young Hong¹, Hee-joong Kim¹, Ha-yun Jeong¹, Sang-hun Song¹, In-tak Cho², Jiyong Noh², Hyun Soo Shin², Kwon-shik Park², Hyun Chul Choi², In Byeong Kang², and Hyuck-in Kwon¹</p> <p>¹<i>School of Electrical and Electronics Engineering, Chung-Ang University,</i> ²<i>Research and Development Center, LG Display Co., Ltd.</i></p>
FC2-H-5 12:00-12:15	<p>The Electrical Performance Difference of TFTs Using SiO_x Gate Insulator Deposited by PECVD and PEALD with DIPAS Precursor</p> <p>Seokgoo Jeong¹, Wanho Choi², Hyun-jun Jeong², Kyungrok Kim², Hyun-mo Lee², Suhwan Choi¹, and Jin-seong Park^{1,2}</p> <p>¹<i>Division of Nanoscale of Semiconductor Engineering, Hanyang University,</i> ²<i>Division of Materials Science and Engineering, Hanyang University</i></p>
FC2-H-6 12:15-12:30	<p>Importance of Substrate Thickness Control on Electrical and Mechanical Operation Robustness of Flexible InGaZnO Thin Film Transistors</p> <p>Hye-won Jang and Sung-min Yoon <i>Department of Advanced Materials Engineering for Information and Electronics, Kyung Hee University</i></p>